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Interplay between intrinsic defects, doping, and free carrier concentration in SrTiO₃ thin films

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Using both computational and experimental analysis, we demonstrate a rich point-defect phase diagram in doped strontium titanate as a function of thermodynamic variables such as oxygen partial pressure and electronic chemical potential. Computational modeling of point-defect energetics demonstrates that a complex interplay exists between dopants, thermodynamic parameters, and intrinsic defects in thin films of SrTiO₃ (STO). We synthesize STO thin films via pulsed laser deposition and explore this interplay between intrinsic defects, doping, compensation, and carrier concentration. Our point-defect analysis (i) demonstrates that careful control over growth conditions can result in the tunable presence of anion and cation vacancies, (ii) suggests that compensation mechanisms will pose intrinsic limits on the dopability of perovskites, and (iii) provides a guide for tailoring the properties of doped perovskite thin films.

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1. INTRODUCTION

The exceptional scope of properties exhibited by perovskite (ABO₃) oxides has catapulted these materials to the forefront of recent research efforts. 1–4 Thin films made from these materials exhibit multiferroicity, 3,4 piezoelectricity, 5 magnetism, 6 colossal magnetoresistance, 7 and ferroelectricity, 8 as well as conductivities that range from insulating to metallic to superconducting. 9 When distinct oxides are deposited in succession on the same substrate, many of these properties can be coupled across heteroepitaxial interfaces. This concept underlies the fields of oxide-based electronics and spintronics, with applications in ultralow-power and high-performance switching, memories, and logic. 4,8,10,11 Device-quality materials, however, require precise control of doping, impose severe demands on film stoichiometry, and require stringent limits on allowable concentrations of unwanted defects. Currently, the (often uncontrolled) presence of defects influences and can even dominate the properties of oxides. 10,12–14 Particularly for low-carrier-density systems, very small (e.g., 1 × 10¹⁸ cm⁻³) differences in defect densities have a striking impact on film properties, particularly electrical properties. 15–17

In this contribution, we explore the equilibrium thermodynamics of point defects in SrTiO₃ (STO) as a function of thermodynamic variables such as oxygen partial pressure and electron chemical potential (Fermi energy). We use density functional theory (DFT) to predict the defect phase diagram for STO and develop a comprehensive point-defect analysis that accounts for the varied defect possibilities in STO. To complement the theoretical predictions, we analyze the stoichiometry of STO thin films grown by pulsed laser deposition (PLD) and show that at extreme thermodynamic conditions, experimental observations are in line with the theoretical predictions. Typically, PLD-grown films are analyzed for defects and nonstoichiometry as a function of laser fluence. In this analysis, we highlight the importance of other thermodynamic variables by fixing the laser fluence. This analysis elucidates the crucial role of growth conditions in the types and concentrations of defects that are present and their interplay. It (i) demonstrates that the defect profile in these thin films exhibits a large sensitivity to the prevailing growth conditions, (ii) confirms recent experimental evidence that both anion and cation vacancies are present in PLD-grown perovskite oxide films, 17,18 (iii) suggests that operative compensation mechanisms pose intrinsic limits to dopability in oxides, and (iv) indicates that careful control over the growth conditions may enable tuning of film composition, defect distribution, and resulting properties such as optical emission, 19 thereby enabling the realization of functional components such as transparent conducting oxides. 20

Vacancies and their complexes are the dominant point defects in most perovskites, and their presence influences electron mobility, 15 electrical conductivity, 16 and physical properties such as defect-induced ferroelectricity in STO 13,14 and defect-driven changes to the thermal conductivity. 21 Perovskite oxide films are often grown by PLD due to its ability to retain stoichiometric cationic transfer when the material is ablated with a laser fluence above the threshold for the material. Recent careful studies on the growth of STO thin films 16,18 have suggested that in STO only a narrow laser fluence range can provide stoichiometric transfer. The defect distribution in thin films realized with high-energy techniques such as PLD are likely dominated by kinetic effects and possible stoichiometric deviations at fractions of a percent. In contrast, low-energy techniques such as molecular beam epitaxy (MBE) may yield compositions closer to stoichiometric and/or defect distributions that are more closely governed by thermodynamics. 22,23 For example,
recently, controlled doping and carrier mobilities as high as 30 000 cm² V⁻¹ s⁻¹ (exceeding those of single crystals) have been demonstrated for epitaxial heterostructures of STO realized by MBE. Moreover, the suppression of cation vacancies has been demonstrated to be consistent with the realization of high doping efficiencies and high mobilities in MBE-grown La-doped STO thin films. It is worth noting that the doping control required to achieve such high mobility is close to a few parts per million (ppm).

We choose doped STO as our model perovskite oxide because it exhibits a large range of measured properties from insulating to superconducting, and because impurity doping of this system has been extensively characterized. STO is largely susceptible to donor doping by cation substitution and via the presence of oxygen vacancies. For example, lanthanum (La), as a substitutional species at the Sr site, is well understood to be an electron donor, under carefully controlled growth conditions, a clear correspondence is established in which one conduction electron is created per La substitution. In STO, the existence of oxygen vacancies (V盱) has long been documented in the literature as well; they are known electron donors that are typically believed to exist in most heterostructures. V盱 are also associated with clustering, blue light emission, and superconductivity, and have been implicated in the high conductivities at the STO/LaAlO3 interface. Understanding the interplay between these vacancies, doping, and other intrinsic defects is critical as high-quality heterostructures with STO are currently avidly pursued for thermoelectric applications, defect- or strain-induced ferroelectricity, electric field-induced superconductivity, and two-dimensional interface conductivity. However, to truly understand this system, a key question is whether the observed phenomena arise either intrinsically or from specious effects due to unknown and undesired defect distributions.

II. COMPUTATION

To determine the types of intrinsic defects—vacancies and their complexes—that are energetically favorable in STO, we first systematically determine defect formation energies for a variety of candidate defects. We expect this comprehensive understanding of stoichiometry and point defects will be most useful for analyzing the properties of thin films synthesized under equilibrium processes. However, although the defect distributions that are present in thin films grown by nonequilibrium techniques are likely governed by kinetic effects, knowledge of defect formation energies as predicted by thermodynamic considerations may still be qualitatively useful even for PLD-grown thin films. A number of previous calculations of defect formation energies in STO have been reported previously (for example, Refs. 26,28,35 and 36); here we present a comprehensive and systematic study for a variety of defects and defect complexes under a wide range of environmental conditions.

A. Density functional theory

We perform calculations based on DFT to determine the formation energies for a variety of native defects, including isolated Sr, Ti, and O vacancies (VSr, VTi, VO), Schottky defects (VSrO), O divacancies (VOO), and complexes of Schottky defects and O vacancies (VSrOO, VO2). The formation energies of SrO, TiO, and TiO2 are given with respect to bulk Sr, bulk Ti, and O2 molecules; the formation energy of STO is given with respect to SrO and TiO2. The correct energy for the O2 molecule is used.

<table>
<thead>
<tr>
<th>Formation energy</th>
<th>DFT-PBE</th>
<th>Expt.</th>
</tr>
</thead>
<tbody>
<tr>
<td>SrO (rocksalt)</td>
<td>−5.93</td>
<td>−6.14 (Ref. 41)</td>
</tr>
<tr>
<td>TiO (rocksalt)</td>
<td>−5.05</td>
<td>−5.62 (Ref. 41)</td>
</tr>
<tr>
<td>TiO2 (rutile)</td>
<td>−10.00</td>
<td>−9.73 (Ref. 41)</td>
</tr>
<tr>
<td>STO (cubic)</td>
<td>−1.21</td>
<td>−1.4 (Ref. 42)</td>
</tr>
</tbody>
</table>

To explore charged defects, electrons are either added to or removed from the supercell containing the defect in the calculation. Since the total energy of a charged supercell with periodic boundary conditions diverges, a compensating jellium background charge is automatically incorporated to render the total energy convergent. Since computed total energies are given with respect to the average electrostatic potential, a potential alignment technique (described below) is used to enable direct comparison of energies for supercells with different charge states.

B. Thermodynamic framework

We compute the defect-formation energies ∆ED,q as

\[ \Delta E_{D,q} = (E_{D,q} - E_{\text{perf}}) - \sum_n n_i \mu_i + q(E_V + E_F), \]  

where E_{D,q} is the (DFT-computed) total energy of the supercell containing a defect \( D \) in the charge state \( q \), E_{\text{perf}} is the (DFT-computed) total energy of the perfect supercell, and \( n_i \) is the number of atoms of species \( i \) added to (\( n_i > 0 \)) or removed from (\( n_i < 0 \)) the supercell to create the defect. Different growth conditions are accommodated by the set of chemical potentials \( \mu_i = \mu_i^{\text{bulk}} + \Delta \mu_i \) for each element by assuming that each is in equilibrium with a physical reservoir such as
where $\Delta \mu_0$ is the occupancy of the deep Kohn-Sham defect level. The high defect concentrations simulated exhibit Moss-Burnstein band-filling effects. The unphysical band-filling effects are eliminated in the manner described here, the band-filling effects are quite small (generally $<0.1$ eV).

Alignment of valence band maxima for charged supercells. The total energies of supercells computed by DFT calculations within the pseudopotential momentum-space formalism are given with respect to the average total electrostatic potential within the supercell. Particularly for the case of charged supercell calculations, it is necessary to ensure that the average electrostatic potentials are aligned for the pure (neutral) host and the charged defect system so that total energies can be consistently compared. Thus, a potential alignment term is added to the defect formation energy in Eq. (1), as described in Ref. 46:

$$\Delta E_{\text{PA}}(D,q) = q \left( V'_d - V'_h \right),$$

where the reference potentials $V'$ within the host $H$ and the charged defect $(D,q)$ supercells are determined by averaging the electrostatic potentials in spheres around atomic sites located far from the defect.

Finite size extrapolation for charged defect-defect interactions. Finally, for charged supercells, the screened interaction energy of the periodically arranged charged defect and the compensating background is estimated by the extrapolation approach described in Refs. 48–50. This approach estimates the charged defect-defect interaction energy arising from

\[ \Delta E_{\text{PA}}(D,q) = q \left( V'_d - V'_h \right), \]
Defect formation energies computed at three points corresponding to low, middle, and high $\Delta \mu_O$ on path $\lambda^1$ (of Fig. 1) are shown in Fig. 3. These are plotted as a function of the Fermi energy $E_F$, which would be in the middle of the gap for intrinsic, stoichiometric STO, and is higher (lower) for n-type (p-type) STO. In Fig. 3, we assume that $E_F$ is an independent (externally controlled) parameter whose value can be fixed via, e.g., the incorporation of impurity dopants such as lanthanum. For $\Delta \mu_O = \Delta \mu_O^{\text{min}}$ (Fig. 3, left), the most favorable defects are, not unexpectedly, $V_O$ and $V_{OO}$ in various charge states. Ionized $V_{Sr}$ and $V_{Ti}$ only become competitive at high $E_F$, serving as compensating acceptors. By contrast, for the highest $\Delta \mu_O = 0$ (Fig. 3, right), the most favorable defects are $V_{Sr}$ and $V_{Ti}$. $V_O$ only become favorable at low $E_F$, serving here as compensating donors. For midranged $\Delta \mu_O = \lambda^1_{\text{min}}/2$ (Fig. 3, middle), as $E_F$ increases, the lowest energy defect shifts from $V_{OO}^+$, the oxygen vacancy in the plus 2 ionized state, to $V_{Sr}^{-2}$. At the midranged values of $E_F$, both $V_{OO}^+$ and $V_{Sr}^{-2}$ are present and may bind together to form the electronically neutral Schottky defect $V_{SrO}$. Overall, we note two trends from Fig. 3. First, as $\Delta \mu_O$ increases, the minimum energy defects shift from $(V_O, V_{OO})$ to $(V_{Sr}, V_{Ti})$, as oxygen vacancies are less favorable (and cation vacancies more favorable) in oxygen-rich environments. Second, as $E_F$ increases from the valence to the conduction band edge, the minimum energy defect shifts from $(V_O, V_{OO})$ to $(V_{Sr}, V_{Ti})$ as the formation of compensating defects becomes more favorable. According to this analysis, compensation mechanisms provide an inherent limitation to supercells, and the approximations introduced by the postprocessing modifications make it nearly impossible to determine quantitatively accurate defect formation energies. To the extent possible, we have invoked estimates of corrections to band-gap and finite size effect errors in a systematic and consistent manner; overall, we find that for most reasonable choices of postprocessing corrections, qualitatively our results remain unchanged and our conclusions and results remain unaltered.

D. Point-defect formation energies

Defect formation energies computed at three points corresponding to low, middle, and high $\Delta \mu_O$ on path $\lambda^1$ (of Fig. 1) are shown in Fig. 3. These are plotted as a function of the Fermi energy $E_F$, which would be in the middle of the gap for intrinsic, stoichiometric STO, and is higher (lower) for n-type (p-type) STO. In Fig. 3, we assume that $E_F$ is an independent (externally controlled) parameter whose value can be fixed via, e.g., the incorporation of impurity dopants such as lanthanum. For $\Delta \mu_O = \Delta \mu_O^{\text{min}}$ (Fig. 3, left), the most favorable defects are, not unexpectedly, $V_O$ and $V_{OO}$ in various charge states. Ionized $V_{Sr}$ and $V_{Ti}$ only become competitive at high $E_F$, serving as compensating acceptors. By contrast, for the highest $\Delta \mu_O = 0$ (Fig. 3, right), the most favorable defects are $V_{Sr}$ and $V_{Ti}$. $V_O$ only become favorable at low $E_F$, serving here as compensating donors. For midranged $\Delta \mu_O = \lambda^1_{\text{min}}/2$ (Fig. 3, middle), as $E_F$ increases, the lowest energy defect shifts from $V_{OO}^+$, the oxygen vacancy in the plus 2 ionized state, to $V_{Sr}^{-2}$. At the midranged values of $E_F$, both $V_{OO}^+$ and $V_{Sr}^{-2}$ are present and may bind together to form the electronically neutral Schottky defect $V_{SrO}$. Overall, we note two trends from Fig. 3. First, as $\Delta \mu_O$ increases, the minimum energy defects shift from $(V_O, V_{OO})$ to $(V_{Sr}, V_{Ti})$, as oxygen vacancies are less favorable (and cation vacancies more favorable) in oxygen-rich environments. Second, as $E_F$ increases from the valence to the conduction band edge, the minimum energy defect shifts from $(V_O, V_{OO})$ to $(V_{Sr}, V_{Ti})$ as the formation of compensating defects becomes more favorable. According to this analysis, compensation mechanisms provide an inherent limitation to supercells, and the approximations introduced by the postprocessing modifications make it nearly impossible to determine quantitatively accurate defect formation energies. To the extent possible, we have invoked estimates of corrections to band-gap and finite size effect errors in a systematic and consistent manner; overall, we find that for most reasonable choices of postprocessing corrections, qualitatively our results remain unchanged and our conclusions and results remain unaltered.
the dopability of SrTiO₃ (similar to, e.g., the amphoteric defect model). \(^5\)

**E. Point-defect phase diagrams**

Using the formalism developed here, we now assess the effect of Sr-poor and Ti-poor growth conditions on the defect distributions. PLD is one of the versatile thin-film growth processes with a complex interplay of parameters determining the growth of the thin-film material. Laser fluence is a common nonequilibrium growth parameter which can be used to tailor the film growth. For example, recent experiments indicate that nonstoichiometric transfer from ceramic targets to films in the PLD process, induced by preferential ablation from the target, can affect Sr/Ti stoichiometry.\(^{16,17}\) Furthermore, positron lifetime measurements indicate that the Sr/Ti stoichiometry can be controlled by laser fluence.\(^{17}\) Meanwhile, our interest is to explore the role of parameters such as oxygen partial pressure and chemical potential (doping level). In Fig. 4, we present point-defect phase diagrams, in which the dominant (lowest-formation-energy) defect is indicated as a function of \(\Delta \mu_o\) and \(E_F\) for the three paths \(\lambda^1\), \(\lambda^2\), and \(\lambda^3\) in Fig. 1. In this figure, the La-dopant concentrations are calculated self-consistently using the charge-neutrality constraint and the mass-action law. In the left panel of Fig. 4 (path \(\lambda^1\), nominally normal Sr/Ti stoichiometry), the dominant defects are shown to be \(V^+_{O}\), \(V^+_1\), and \(V^+_2\). The two trends discussed above are evident in this panel: the defect distribution shifts from anion to cation vacancies with increasing \(\Delta \mu_o\) and increasing \(E_F\). Note how reduced the effect of doping with 15% La is due to the low formation energy of compensating \(V_{Sr}\). In the middle panel of Fig. 4, the dominant defect is shown for the case of Sr-poor growth, corresponding to path \(\lambda^2\) of Fig. 1. The two trends persist; however, the regime for which \(V_{Sr}\) and \(V_{Sr0}\) are dominant is expanded. This growth regime would be particularly unfavorable for La doping, as compensating \(V_{Sr}\) renders it very difficult to introduce free electrons. For the Ti-poor growth regime of path \(\lambda^3\) (Fig. 4, right), the \(V_{Ti}\) regime grows at the expense of \(V_{Sr}\) and \(V_{Sr0}\), and the capacity for external doping to create free electrons is recovered due to the overall higher formation energy of the prevailing compensating species \(V_{Ti}\). If indeed the Sr/Ti ratio can be controlled by laser fluence,\(^{17}\) the three panels of Fig. 4 suggest a reason for the seemingly contradictory reports of vacancy defect characteristics that have been reported for PLD growth in terms of a high sensitivity of the defect distribution to the growth conditions. Our analysis suggests that target growth windows, in terms of Sr/Ti stoichiometry, can maximize the effects of extrinsic doping, illustrating how controlled use of laser fluence, oxygen pressure, and dopant concentration may offer routes to more controlled defect compositions and film properties in PLD-grown systems.

**III. EXPERIMENTS AND DISCUSSION**

The phase diagrams presented in Fig. 4 indicate that careful control over thermodynamic parameters may result in tunability of defect profiles. To explore the applicability of the point-defect analysis to real STO thin films, we synthesize and characterize a number of STO thin films via PLD as described below. Strictly (as discussed above), the applicability of the thermodynamic framework is best suited for thin films grown under near-equilibrium conditions and a quantitative comparison is not expected. However, we wish to assess whether thermodynamic variables such as oxygen partial pressure and electron chemical potential affect the stoichiometry of films grown via high-energy techniques such as PLD, and whether this effect can be qualitatively explained using the thermodynamic framework developed above.

Thin films of doped STO were grown using pulsed laser deposition. These films were grown using a KrF excimer laser with a laser fluence of 1.5 J cm\(^{-2}\) over a range of growth pressures (in oxygen partial pressure \(P(O_2)\)) from 100 mTorr to 10\(^{-3}\) Torr. To minimize the possibility that nonstoichiometry could arise from different ablation conditions, we grew all the samples with the same fluence and spot area, and we have used the same laser fluence as in Ref. 21, which we believe to be optimal for stoichiometric transfer. The growth temperature as measured by the thermocouple attached to the substrate heater was set at 850 °C. The oxygen partial pressure during the growth was varied between \(1 \times 10^{-1}\) and \(1 \times 10^{-8}\) Torr,
Large dependence on Measured carrier concentrations exhibit a large sensitivity to the measurements, of PLD-grown STO films vs La content for growth electron carrier concentration as a function of the La content of La doping. By contrast, at low $P_{O_2}$ serve to reduce the measured carrier concentrations at fixed $P_{O_2}$, demonstrating that thermodynamic parameters influence the properties of PLD-grown thin films. The measured carrier concentrations are generally lower than expected from the La doping alone if the thin films were otherwise stoichiometric (indicated by the dotted line). This observation is consistent with the presence of compensating species such as $V_{Sr}$ and $V_{Ti}$ predicted by the point-defect analysis. Furthermore, the measured carrier concentrations parallel the trends we identified in Figs. 3 and 4. For instance, we note that for a fixed La concentration, the measured carrier concentration in Fig. 5 (and thus $E_F$) decreases as $P_{O_2}$ increases. This trend can also be seen in the phase diagrams of Fig. 4, in which the lower defect formation energies of the compensating cation vacancies at high $P_{O_2}$ serve to reduce the measured carrier concentrations at fixed La doping. By contrast, at low $P_{O_2}$ the measured carrier concentrations are higher, because the defect profile shifts toward oxygen vacancies and renders the formation of the compensating cation vacancies more difficult.

We note that experimentally accessible values of $T$ and $P_{O_2}$ correspond to $-2 < \Delta \mu_O < 0$ eV according to data in Ref. 41; this corresponds roughly to the second and third panels of Fig. 3. In this regime, when STO is doped with donors such as La, cation vacancies exhibit the lowest formation energies. It is interesting that in most PLD-grown STO, the existence of $V_O$ has been long documented whereas the cation vacancies $V_{Sr}$ and $V_{Ti}$ have traditionally received less attention. However, their relevance has also recently become more appreciated: they have been implicated in defect-induced ferroelectricity as well as the suppression of donor doping in STO. Signatures of their existence have recently been observed in PLD-grown homoepitaxial STO layers via positron annihilation lifetime spectroscopy measurements, and the lattice constant expansion that is often observed in PLD-grown films and attributed to $V_O$ was shown to also be consistent with cation vacancies. Our analysis suggests that the presence of $V_O$ arises mainly from the kinetic inhibition of oxygen incorporation into the growing thin film (as they are not favored by their equilibrium formation energies), resulting in locally much lower $\Delta \mu_O$ than the experimentally accessible range. Hence, the point-defect analysis is consistent with the presence of both cation and anion vacancies and suggests that their relative concentrations can be tuned by $P_{O_2}$ and/or degree of external doping as suggested in Figs. 3 and 5. We also comment on $V_{O_{2O}}$, because oxygen vacancy clustering is often implicated in the blue light emission observed in STO: according to our analysis and in contrast to the findings of Ref. 28, when charged defects are considered, we find that clustering of $V_O$ is not particularly favorable, a result of the electrostatic repulsion arising from the fact that $V_O$ tend to be charged.

To further explore whether the sensitivity of the carrier concentration to $P_{O_2}$ during growth observed in Fig. 5 can be attributed to stoichiometric variations, we perform time-of-flight ion scattering and recoil spectroscopy (TOF-ISARS) measurements on our samples. In these measurements [see inset in Fig. 6(a)], a primary ion beam of $^{39}K$ ions with a kinetic energy of 10 keV is directed at the sample. An Ionwerks (Houston, USA) mass spectrometer of recoiled ions (MSRI) reflectron detector was used to detect the recoiled species. The MSRI detector was fixed at a 60° angle to the incident ion beam. The angles of incidence used at the sample are 15° and 30° (for the 30° case, the shadowing regions and blocking cones are directed more downward, which is expected to give a better representation of the subsurface film layers). Figure 6 plots the relative intensities for various atomic species registered by the MSRI detector, normalized to the primary ion signal, and plotted as a function of the azimuthal angle δ (denoting the orientation of the film surface with respect to the incident beam). The minima and maxima in the spectra reflect the crystalline directions where different species are blocking each other or presenting a free path, respectively.

Data are shown for both pure and La-doped STO grown under high and low $P_{O_2}$. Figure 6(a) shows the TOF relative intensity for Sr and La recoiled from La-doped STO films grown at both low and high $P_{O_2}$. While the La signal is similar for the two growth pressures, a clear difference is observed in the Sr signal. Consistent with our Hall measurements, the Sr intensity is higher at low $P_{O_2}$, suggesting that growth at low $P_{O_2}$ results in the incorporation of more Sr into the films. This is also consistent with our point-defect analysis, which suggests a shift from $V_{Sr}$ to $V_O$ as the oxygen partial pressure decreases to further inhibit the formation of carrier-compensating defects. Thus, even under high-energy (nonequilibrium) growth conditions, it appears that thermodynamic quantities such as growth pressure and defect formation energies exhibit an influence.

FIG. 5. (Color online) Carrier density, obtained from Hall effect measurements, of PLD-grown STO films vs La content for growth at different oxygen partial pressures. Dashed line: carrier density predicted by La concentration in otherwise stoichiometric films. Measured carrier concentrations exhibit a large sensitivity to the oxygen partial pressure.
FIG. 6. (Color online) Time-of-flight ion scattering and recoil spectroscopy measurements on pure and La-doped STO thin films indicate Sr deficiency (or O excess) when films are synthesized at high $P_{O_2}$. (a) Counts registered by the MSRI detector, normalized to the scattered potassium signal, for La-doped STO grown at high and low $P_{O_2}$. Although the La signal is similar for both cases, the Sr signal is notably lower for films synthesized at high $P_{O_2}$. (The experimental setup is shown in the inset.) (b) and (c) Counts registered by the MSRI detector, normalized to the scattered potassium signal, for pure STO grown at high and low $P_{O_2}$ for beam incident at 15° and 30°, respectively. Again, while Ti count is similar for high and low $P_{O_2}$, Sr count is smaller at high $P_{O_2}$ and larger at low $P_{O_2}$.

on the defect characteristics of the films. In Figs. 6(b) and 6(c), TOF results are shown for pure STO for incident angles of 15° and 30°, respectively. Again, the difference in the Sr signals for growth at high and low $P_{O_2}$ is clearly observable [particularly near the peaks in Fig. 6(c)]. These results indicate that, even in undoped STO, systems grown at low $P_{O_2}$ are more Sr rich than those grown at high $P_{O_2}$: this is consistent with the point-defect model and the carrier concentration measurements, which predict a shift from anion to cation vacancies as $P_{O_2}$ increases. Although the result of variable cation stoichiometry with $P_{O_2}$ may be surprising, similar observations have been previously reported. For example, our observation is in excellent agreement with investigations on the electrical conductivity as a function of oxygen pressure on thin films and crystals of STO and with the demonstration of the use of $P_{O_2}$ for controlled cation stoichiometry in STO thin films.

Finally, we give an example of the application of our analysis to the recent demonstration of transparent conducting oxides (TCOs) made from double-doped STO. The unusual combination of electronic and optical properties that are necessary for a material to conduct electrons while remaining transparent to visible light is most often related to the presence of shallow donor states close to the conduction band edge (green circles in Fig. 3). Furthermore, in undoped STO, the number of oxygen vacancies are roughly offset by the number of strontium vacancies (for instance, in Fig. 4, left panel), and the oxygen defect levels are thus mostly empty. However, incorporation of the appropriate quantities of La dopants through nonequilibrium doping, especially in growth regimes when compensation mechanisms are unfavorable, may provide avenues to control the filling of these defect levels as necessary to achieve a TCO, as indicated in Ref.

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18Rigorously, for a defect-forming reaction at a given temperature and pressure, the governing thermodynamic potential is the Gibbs free energy 

\[ \Delta G_{D_q}(T, P) \]

However, we assume that the entropic contribution to and the pressure dependence of the free energy are negligible compared to the internal energy contribution, so that

\[ \Delta G_{D_q}(T, P) \approx \Delta E_{D,q} \]


